
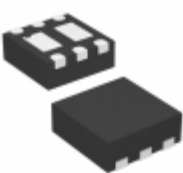
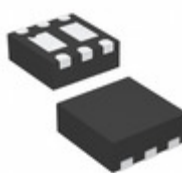
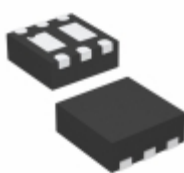
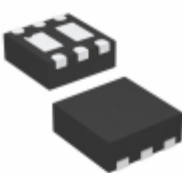
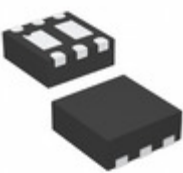
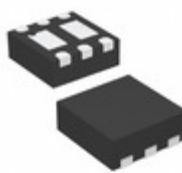
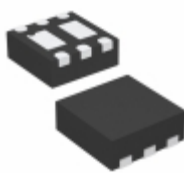
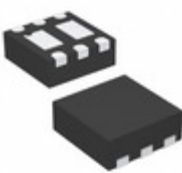
	<h2>SIA778DJ-T1-GE3</h2>
	<p><b>Hersteller-Teilenummer:</b> SIA778DJ-T1-GE3</p> <p><b>Hersteller / Marke:</b> Electro-Films (EFI) / Vishay</p> <p><b>Teil der Beschreibung:</b> MOSFET 2N-CH 12V/20V SC70-6</p> <p><b>Datenblätter:</b>  <a href="#">SIA778DJ-T1-GE3.pdf</a></p> <p><b>RoHs Status:</b> Bleifrei / RoHS-konform</p> <p><b>Lagerzustand:</b> New original, 10000 pcs Stock Available.</p> <p><b>Liefern von:</b> Hong Kong</p> <p><b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

### Spezifikationen

Teilenummer	SIA778DJ-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET 2N-CH 12V/20V SC70-6
Kategorie	<a href="#">Diskrete Halbleiterprodukte</a> > <a href="#">Transistoren-FETs</a> ,
Teilstatus	10000 pcs Stock
Hersteller Standard Vorlaufzeit	27 Weeks
detaillierte Beschreibung	Mosfet Array 2 N-Channel (Dual) 12V, 20V 4.5A, 1.5A
Serie	TrenchFET®
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Leistung - max	6.5W, 5W
Verpackung / Gehäuse	PowerPAK® SC-70-6 Dual
Supplier Device-Gehäuse	PowerPAK® SC-70-6 Dual
Typ FET	2 N-Channel (Dual)
FET-Merkmal	Logic Level Gate
Drain-Source-Spannung (Vdss)	12V, 20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	4.5A, 1.5A
Rds On (Max) @ Id, Vgs	29 mOhm @ 5A, 4.5V
VGS (th) (Max) @ Id	1V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	15nC @ 8V
Eingabekapazität (Ciss) (Max) @ Vds	500pF @ 6V
Verpackung	Tape & Reel (TR)
Basisteilenummer	SIA778
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SIA778DJ-T1-GE3TR

SIA778DJ-T1-GE3 ist neu im Original, Suche SIA778DJ-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SIA778DJ-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SIA778DJ-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p><b>SIA537EDJ-T1-GE3</b> Vishay / Siliconix MOSFET N/P-CH 12V/20V SC-70-6L</p>	 <p><b>SIA537EDJ-T1-GE3</b> Electro-Films (EFI) / Vishay MOSFET N/P-CH 12V/20V SC-70-6L</p>	 <p><b>SIA777EDJ-T1-GE3</b> Vishay / Siliconix MOSFET N/P-CH 20V/12V SC70-6L</p>	 <p><b>SIA810DJ-T1-E3</b> Vishay / Siliconix MOSFET N-CH 20V 4.5A SC-70-6</p>
 <p><b>SIA811ADJ-T1-GE3</b> Electro-Films (EFI) / Vishay MOSFET P-CH 20V 4.5A PPAK SC70-6</p>	 <p><b>SIA810DJ-T1-E3</b> Electro-Films (EFI) / Vishay MOSFET N-CH 20V 4.5A SC-70-6</p>	 <p><b>SIA810DJ-T1-GE3</b> Vishay / Siliconix MOSFET N-CH 20V 4.5A SC70-6</p>	 <p><b>SIA810DJ-T1-GE3</b> Electro-Films (EFI) / Vishay MOSFET N-CH 20V 4.5A SC70-6</p>

heiße Teile

Mehr

⊕ SIA445EDJ-T1-GE3	↔ SIA447DJ-T1-GE3	⇒ SIA447DJ-T1-GE3	D SIA448DJ-T1-GE3	⇒ SIA448DJ-T1-GE3
⊕ SIA449DJ-GE3	⊕ SIA450DJ-T1-GE3	D SIA450DJ-T1-GE3	⇒ SIA4528-100K	⇒ SIA4528-330K
⊕ SIA4528-470K	⊕ SIA453EDJ-T1-GE3	⊕ SIA453EDJ-T1-GE3	↔ SIA456DJ-T1-GE3	⇒ SIA456DJ-T1-GE3
D SIA483DJ-T1-GE3	⊕ SIA483DJ-T1-GE3	⊕ SIA513DJ-T1-E3	⊕ SIA517DJ-T1-GE3	⇒ SIA517DJ-T1-GE3
⇒ SIA517DJ-T4-GE3	↔ SIA519EDJ-T1-GE3	⊕ SIA519EDJ-T1-GE3	⊕ SIA533EDJ-T1-GE3	⇒ SIA533EDJ-T1-GE3
↔ SIA778DJ-T1-GE3	⇒ SIA811ADJ-T1-GE3	D SIA811ADJ-T1-GE3	⊕ SIA811DJ-T1	⊕ SIA811DJ-T1-E3
⊕ SIA811DJ-T1-E3	D SIA811DJ-T1-GE3	⇒ SIA811DJ-T1-GE3	↔ SIA813DJ-T1-GE3	⇒ SIA813DJ-T1-GE3
⊕ SIA814DJ-T1-GE3	⊕ SIA814DJ-T1-GE3	↔ SIA906EDJ-T1-GE3	⇒ SIA906EDJ-T1-GE3	⇒ SIA906EDJ-T4-GE3
⊕ SIA907EDJT	⊕ SIA907EDJT-T1-GE3	⊕ SIA907EDJT-T1-GE3	D SIA907EDJT-T4-GE3	⇒ SIA910EDJ-T1-GE3
↔ SIA910EDJ-T1-GE3	⊕ SIA911ADJ-T1-GE3	⊕ SIA911ADJ-T1-GE3	⊕ SIA911ADJ-T5-GE3	⇒ SIA911DJ-T1-E3

Contact us: [Info@Y-IC.com](mailto:Info@Y-IC.com)

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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